

# Thyristor

$$V_{RRM} = 1200\text{ V}$$

$$I_{TAV} = 45\text{ A}$$

$$V_T = 1.37\text{ V}$$

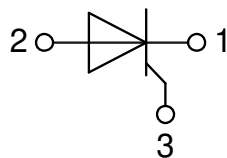
## Single Thyristor

Part number

**CS45-12io1**



Backside: anode



### Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

### Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

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Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		50	$\mu A$
		$V_{R/D} = 1200 V$	$T_{VJ} = 125^{\circ}C$		3	mA
$V_T$	forward voltage drop	$I_T = 45 A$	$T_{VJ} = 25^{\circ}C$		1.36	V
		$I_T = 90 A$			1.73	V
		$I_T = 45 A$	$T_{VJ} = 125^{\circ}C$		1.37	V
		$I_T = 90 A$			1.85	V
$I_{TAV}$	average forward current	$T_C = 110^{\circ}C$	$T_{VJ} = 150^{\circ}C$		45	A
$I_{T(RMS)}$	RMS forward current	180° sine			71	A
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0.88	V
$r_T$	slope resistance				11	m $\Omega$
$R_{thJC}$	thermal resistance junction to case				0.4	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.3		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		310	W
$I_{TSM}$	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$		520	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$		560	A
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}C$		440	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$		475	A
$I^2t$	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$		1.35	kA <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$		1.31	kA <sup>2</sup> s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}C$		970	A <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$		940	A <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400 V$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		22	pF
$P_{GM}$	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		10	W
		$t_p = 300 \mu s$			5	W
$P_{GAV}$	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}C$ ; f = 50 Hz	repetitive, $I_T = 135 A$		150	A/ $\mu s$
		$t_p = 200 \mu s$ ; $di_G/dt = 0.3 A/\mu s$ ; $I_G = 0.3 A$ ; $V = \frac{2}{3} V_{DRM}$	non-repet., $I_T = 45 A$		500	A/ $\mu s$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)	$T_{VJ} = 125^{\circ}C$		1000	V/ $\mu s$
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1.5	V
			$T_{VJ} = -40^{\circ}C$		1.6	V
$I_{GT}$	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		80	mA
			$T_{VJ} = -40^{\circ}C$		200	mA
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}C$		0.2	V
$I_{GD}$	gate non-trigger current				10	mA
$I_L$	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		150	mA
		$I_G = 0.3 A$ ; $di_G/dt = 0.3 A/\mu s$				
$I_H$	holding current	$V_D = 6 V$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		100	mA
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	$\mu s$
		$I_G = 0.3 A$ ; $di_G/dt = 0.3 A/\mu s$				
$t_q$	turn-off time	$V_R = 100 V$ ; $I_T = 45 A$ ; $V = \frac{2}{3} V_{DRM}$ $di/dt = 15 A/\mu s$ $dv/dt = 20 V/\mu s$ $t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		150	$\mu s$



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		20		120	N

**Product Marking**



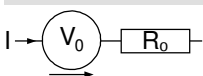
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CS45-12io1	CS45-12io1	Tube	30	467685

Similar Part	Package	Voltage class
CS45-08io1	TO-247AD (3)	800
CS45-16io1	TO-247AD (3)	1600
CS45-16io1R	ISOPLUS247 (3)	1600
CLA50E1200HB	TO-247AD (3)	1200

**Equivalent Circuits for Simulation**

*\* on die level*

$T_{VJ} = 150^{\circ}C$



**Thyristor**

$V_{0\ max}$	threshold voltage	0.88	V
$R_{0\ max}$	slope resistance *	8.5	mΩ



**Outlines TO-247**



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



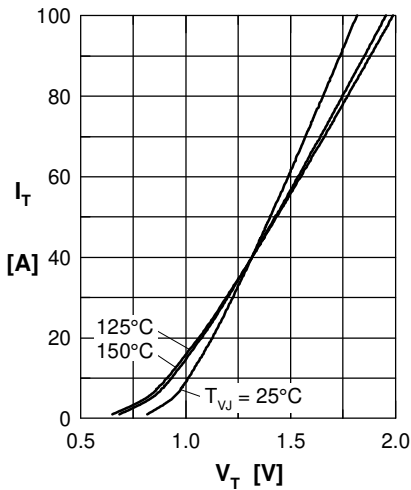
**Thyristor**


Fig. 1 Forward characteristics

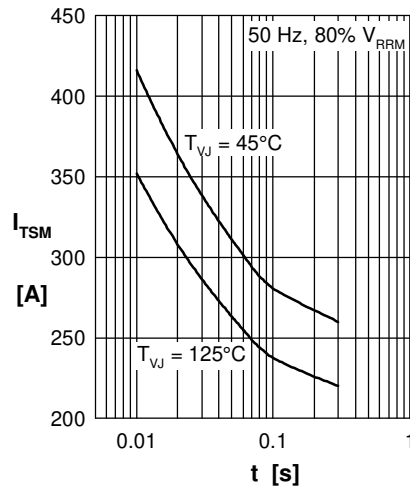


Fig. 2 Surge overload current

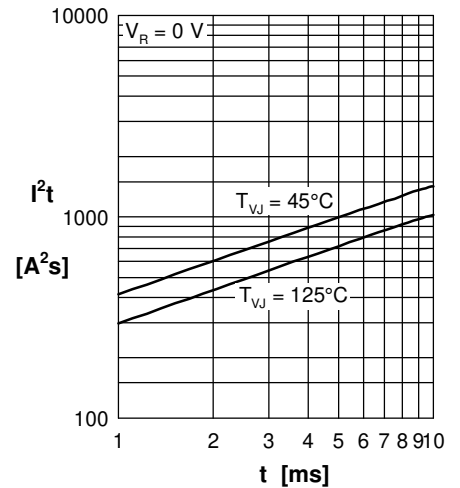
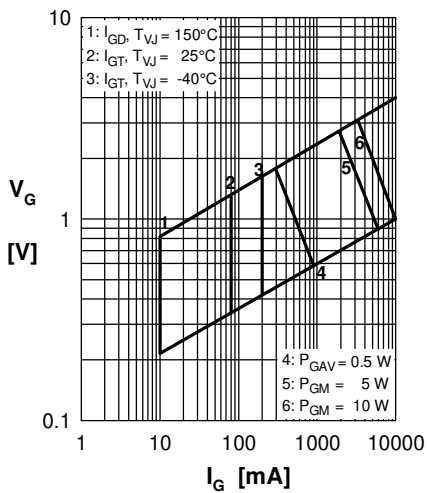

 Fig. 3  $I^2t$  versus time (1-10 ms)


Fig. 4 Gate trigger characteristics

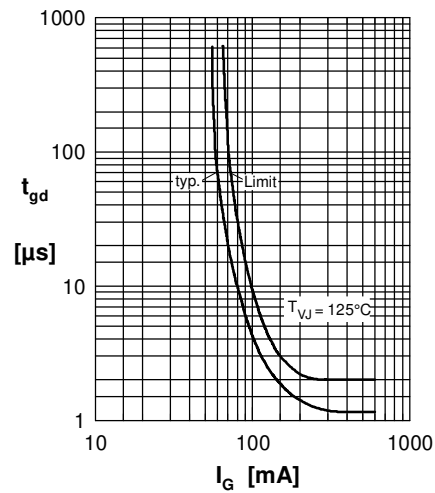


Fig. 5 Gate controlled delay time

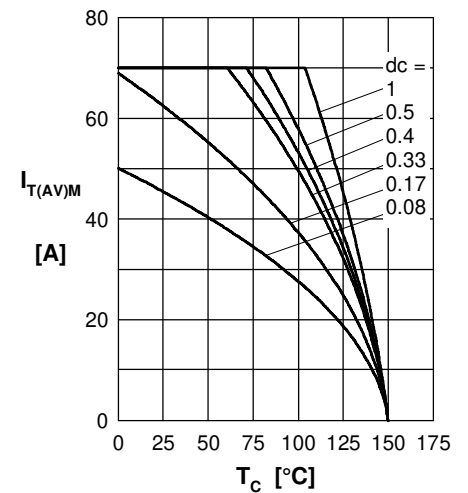


Fig. 6 Max. forward current at case temperature

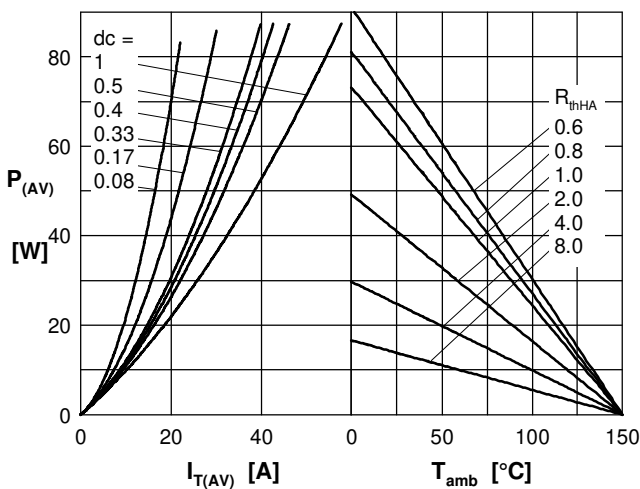
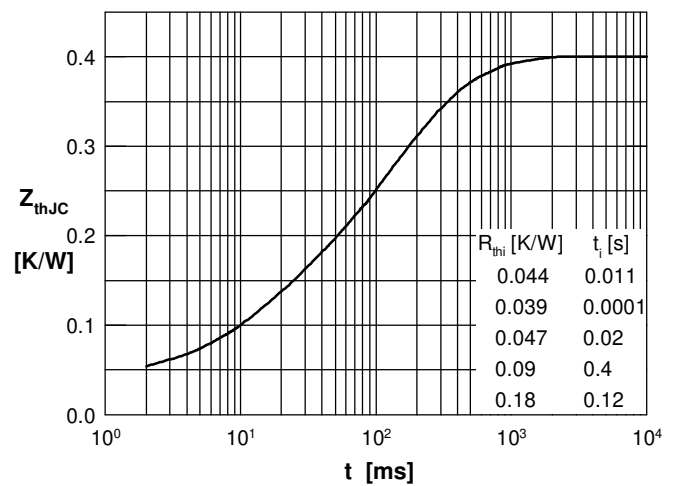

 Fig. 7a Power dissipation versus direct output current  
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case